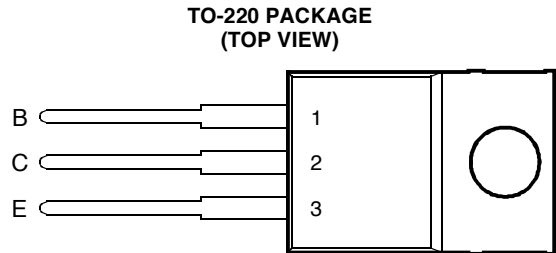


BD243, BD243A, BD243B, BD243C NPN SILICON POWER TRANSISTORS



- Designed for Complementary Use with the BD244 Series
- 65 W at 25°C Case Temperature
- 6 A Continuous Collector Current
- 10 A Peak Collector Current
- Customer-Specified Selections Available
- “-S” Suffix Added to Part Number Indicates RoHS Compliance*



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD243	V_{CER}	55	V
	BD243A		70	
	BD243B		90	
	BD243C		115	
Collector-emitter voltage ($I_C = 30 \text{ mA}$)	BD243	V_{CEO}	45	V
	BD243A		60	
	BD243B		80	
	BD243C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	6	A
Peak collector current (see Note 1)		I_{CM}	10	A
Continuous base current		I_B	3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	65	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	62.5	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

- NOTES: 1. This value applies for $t_p \leq 0.3 \text{ ms}$, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.52 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20 \text{ mH}$, $I_{B(on)} = 0.4 \text{ A}$, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20 \text{ V}$.

*RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

PRODUCT INFORMATION

JUNE 1973 - REVISED NOVEMBER 2012
 Specifications are subject to change without notice.

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5)	$I_B = 0$	BD243	45			V
			BD243A	60			
			BD243B	80			
			BD243C	100			
I_{CES} Collector-emitter cut-off current	$V_{CE} = 55 \text{ V}$ $V_{CE} = 70 \text{ V}$ $V_{CE} = 90 \text{ V}$ $V_{CE} = 115 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD243			0.4	mA
			BD243A			0.4	
			BD243B			0.4	
			BD243C			0.4	
I_{CEO} Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$	BD243/243A			0.7	mA
			BD243B/243C			0.7	
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 0.3 \text{ A}$ $I_C = 3 \text{ A}$	(see Notes 5 and 6)	30			
				15			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 1 \text{ A}$	$I_C = 6 \text{ A}$	(see Notes 5 and 6)			1.5	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 6 \text{ A}$	(see Notes 5 and 6)			2	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.92	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 1 \text{ A}$ $V_{BE(off)} = -3.7 \text{ V}$	$I_{B(on)} = 0.1 \text{ A}$ $R_L = 20 \Omega$	$I_{B(off)} = -0.1 \text{ A}$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		0.3		μs
t_{off} Turn-off time					1		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

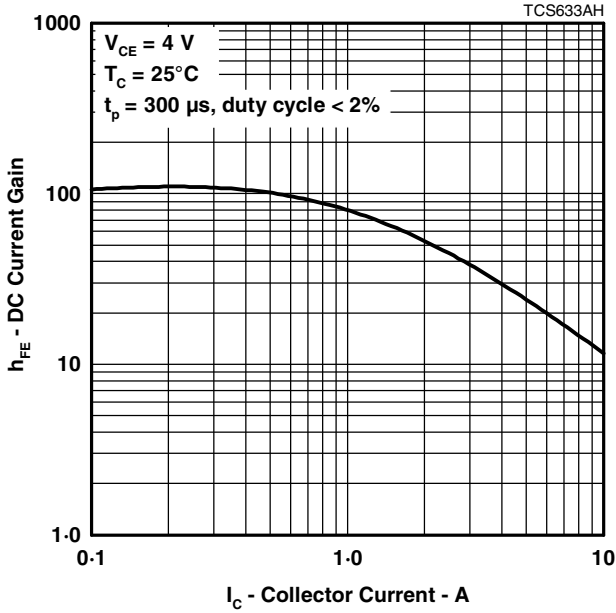


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
BASE CURRENT

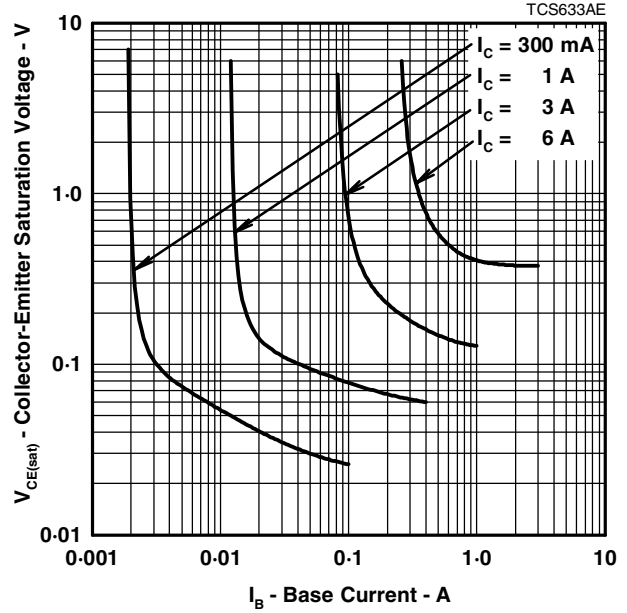


Figure 2.

BASE-EMITTER VOLTAGE
VS
COLLECTOR CURRENT

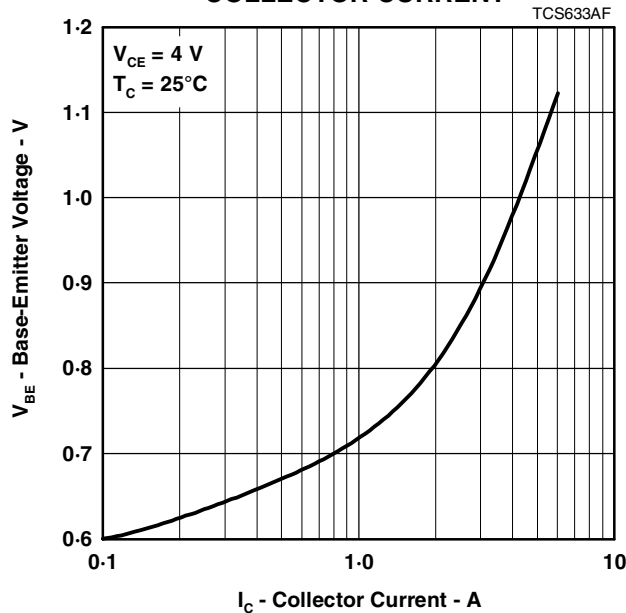
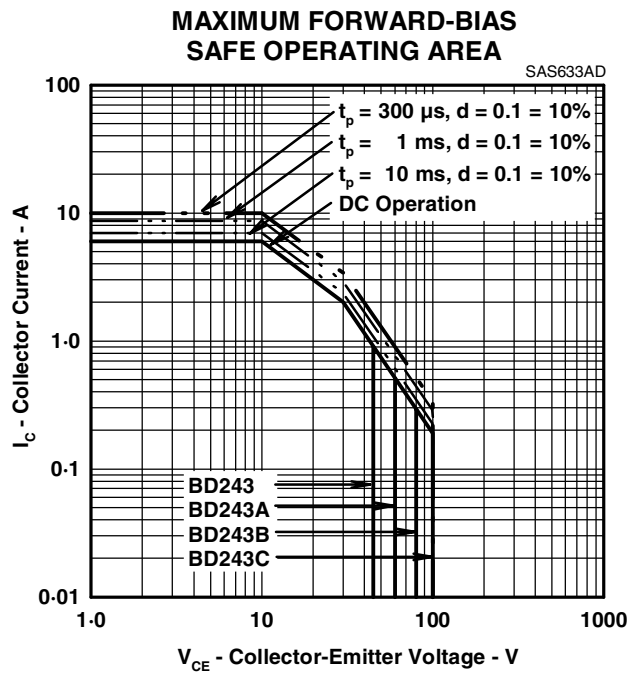


Figure 3.

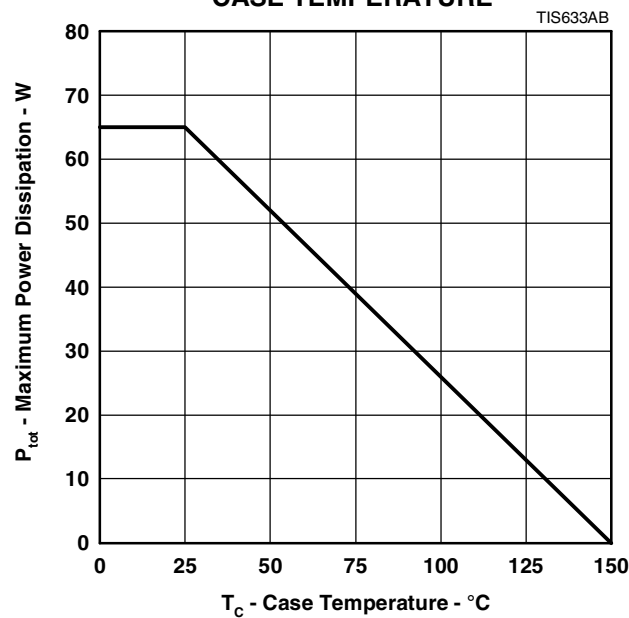
PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**



PRODUCT INFORMATION